# MSD1819A-RT1G, NSVMSD1819A-RT1G

# **General Purpose Amplifier Transistor**

#### **NPN Silicon Surface Mount**

This NPN Silicon Epitaxial Planar Transistor is designed for general purpose amplifier applications. This device is housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

#### **Features**

- High h<sub>FE</sub>, 210-460
- Low V<sub>CE(sat)</sub>, < 0.5 V
- Moisture Sensitivity Level 1
- ESD Protection:
  - ♦ Human Body Model > 4000 V
  - ◆ Machine Model > 400 V
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>(BR)CBO</sub>	60	Vdc
Collector-Emitter Voltage	V <sub>(BR)CEO</sub>	50	Vdc
Emitter-Base Voltage	V <sub>(BR)EBO</sub>	7.0	Vdc
Collector Current – Continuous	Ic	100	mAdc
Collector Current - Peak	I <sub>C(P)</sub>	200	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 1)	P <sub>D</sub>	150	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

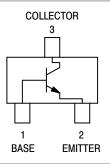


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SC-70 (SOT-323) CASE 419 STYLE 3



#### **MARKING DIAGRAM**



ZR = Device Code
M = Date Code\*
• Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MSD1819A-RT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
NSVMSD1819A-RT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### MSD1819A-RT1G, NSVMSD1819A-RT1G

#### **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 2.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	-	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	60	-	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 10 \mu Adc, I_E = 0$ )	V <sub>(BR)EBO</sub>	7.0	_	Vdc
Collector-Base Cutoff Current (V <sub>CB</sub> = 20 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	0.1	μΑ
Collector-Emitter Cutoff Current (V <sub>CE</sub> = 10 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	0.1	μΑ
DC Current Gain (Note 2) ( $V_{CE} = 10 \text{ Vdc}$ , $I_{C} = 2.0 \text{ mAdc}$ ) ( $V_{CE} = 2.0 \text{ Vdc}$ , $I_{C} = 100 \text{ mAdc}$ )	h <sub>FE1</sub> h <sub>FE2</sub>	210 90	340 -	-
Collector-Emitter Saturation Voltage (Note 2) (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 10 mAdc)	V <sub>CE(sat)</sub>	_	0.5	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

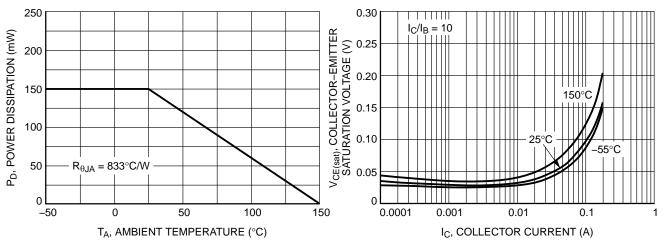


Figure 1. Derating Curve

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

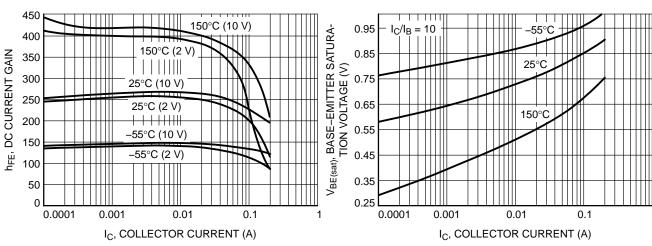
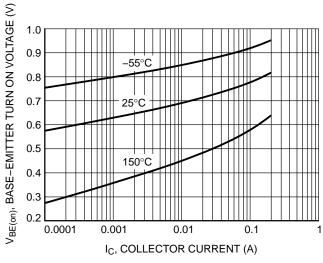


Figure 3. DC Current Gain vs. Collector Current

Figure 4. Base Emitter Saturation Voltage vs.
Collector Current

<sup>2.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, D.C.  $\leq$  2%.

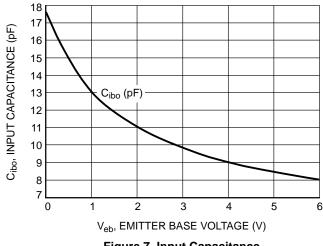
### MSD1819A-RT1G, NSVMSD1819A-RT1G



V<sub>CE</sub>, COLLECTOR-EMITTER VOLTAGE (V) 1.2 1.0 = 100 mA50 mA 10 mA 0.8 0.6 0.4 0.2 0.000001 0.00001 0.0001 0.001 IB, BASE CURRENT (A)

Figure 5. Base Emitter Turn-On Voltage vs. **Collector Current** 

Figure 6. Collector Saturation Region



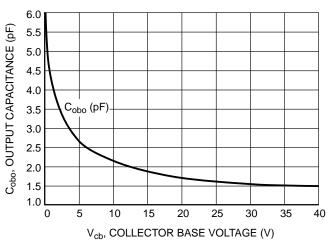


Figure 7. Input Capacitance

Figure 8. Output Capacitance

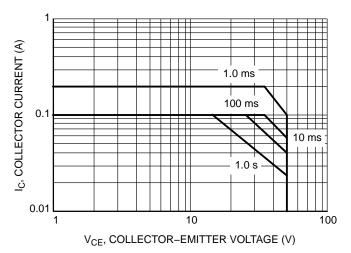


Figure 9. Safe Operating Area





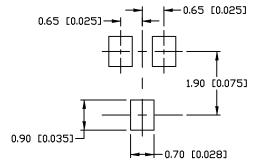
SC-70 (SOT-323) CASE 419 ISSUE P

**DATE 07 OCT 2021** 

#### NOTES:

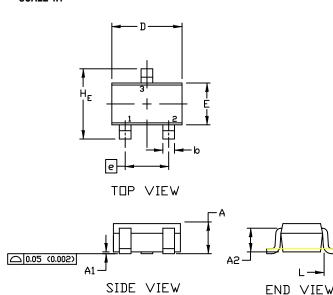
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 BS	C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
Ε	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095
				`		



For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SILDERRM/D.

SOLDERING FOOTPRINT



# GENERIC MARKING DIAGRAM



XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
3. COLLECTOR	3. COLLECTOR	3. DRAIN	3. CATHODE-ANODE	3. ANODE-CATHODE	3. CATHODE

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DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1	

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